

PRM012N04S8

PFC Device Corporation

40V Single N-Channel MOSFET

Major ratings and characteristics

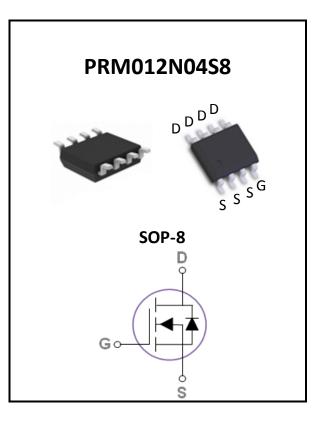
Characteristics	Values	Units
V _{DS}	40	V
I _D (T _A =25°C)	10.7	Α
Max. R _{DS(ON)} @V _{GS} =10V	12	mΩ
Max. $R_{DS(ON)}@V_{GS}=4.5V$	17	mΩ
T _J Operating Junction Temperature	-55 to +150	°C

General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting



Features

- Max. $R_{DS(ON)}=12m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
	Drain Current – Continuous (T _A =25°C)	10.7	А
Ι _D	Drain Current – Continuous (T _A =100°C)	6.7	А
I _{DM}	Drain Current – Pulsed ¹	42.8	А
E _{AS}	Single Pulse Avalanche Energy ²	5	mJ
I _{AS}	Single Pulse Avalanche Current ²	10	А
Р	Power Dissipation (T _A =25°C)	2.5	W
P _D	Power Dissipation – Derate above 25°C	0.02	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to Ambient		50	°C/W



Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40			V
	Drain Source Leekage Current	V _{DS} =40V, V _{GS} =0V, T _J =25°C			1	uA
IDSS	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V, T _J =125°C			250	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA

On Characteristics

R _{DS(ON)} Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5A			12	mΩ	
R _{DS(ON)}		V _{GS} =4.5V, I _D =3A			17	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0		3.0	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A		19		S

Dynamic and switching Characteristics

Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _D =10.7A	 24	
Q _{gs}	Gate-Source Charge		 4.5	 nC
Q _{gd}	Gate-Drain Charge		 4	
T _{d(on)}	Turn-On Delay Time		 11	
Tr	Turn-On Rise Time	V_{DD} =20V, V_{GS} =10V, R_{G} =6 Ω I_{D} =10.7A	 56	 ns
T _{d(off)}	Turn-Off Delay Time		 29	 115
T _f	Turn-Off Fall Time		 55	
C _{iss}	Input Capacitance		 1390	
C _{oss}	Output Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	 100	 pF
C _{rss}	Reverse Transfer Capacitance		 75	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	 2	 Ω

Drain-Source Diode Characteristics

V _{SD} ³	Source to Drain Diode Voltage	V _{GS} =0V, I _S =10.7A	 	1.5	V
t _{rr}	Reverse Recovery Time	I _s =10A, di/dt=100A/us	 7		ns
Q _{rr}	Reverse Recovery Charge	$I_{\rm S}$ = 10A, u/ul= 100A/us	 1		nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.

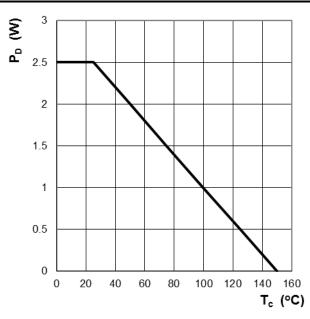
2. L=0.1mH, R_G =25 Ω , Starting T_J=25°C

3. The data tested by pulsed , pulse width $\leq\!\!300us$, duty cycle $\leq\!\!2\%$





Ratings and Characteristics Curves





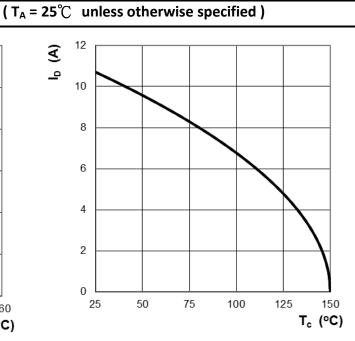
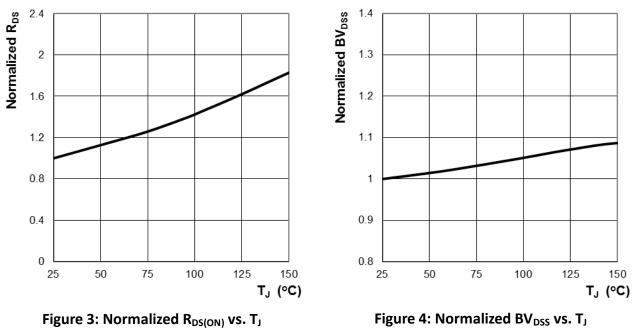
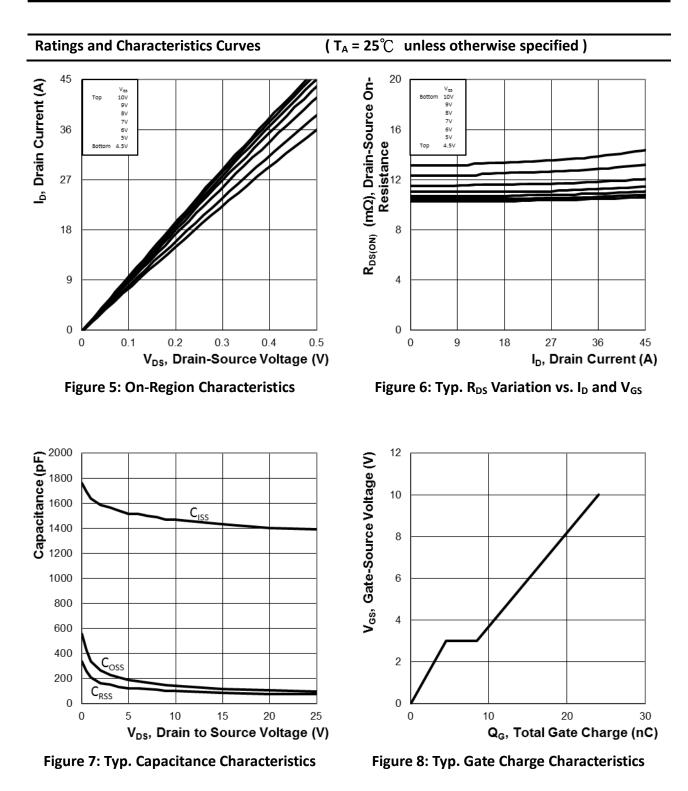


Figure 2: Continuous Drain Current vs. T_c

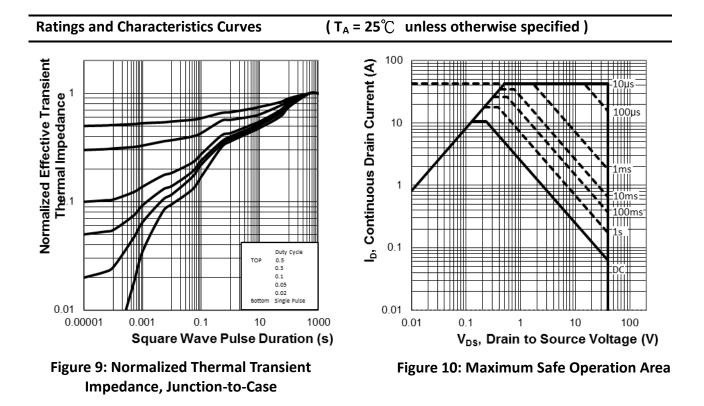








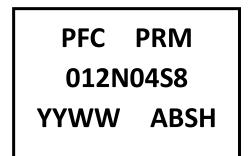






3. Marking information

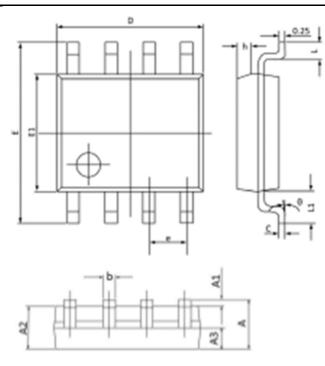
Top Marking Rule



PRM012N04S8 = Product Type Marking Code YYWW = Date Code YY = Last two digits of year WW = Week code ABS = Assembly code H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters



Dim.	Min.	Max.		
Α	1.35	1.75		
Al	0.10	0.25		
A2	1.30			
A3	0.60	0.70		
b	0.35	0.49		
С	0.18	0.26		
D	4.70	5.10		
E	5.80	6.20		
El	3.70	4.10		
e	1.27	BSC		
h	0.25	0.50		
L	0.40	0.90		
Ll	1.05 BSC			
θ	0°	8°		
All Dimensions in mm				



5. Ordering information

Part Number	Package	Delivery mode
PRM012N04S8	SOP-8	3000 pcs / 13" diameter reel

Mechanical

- Molder Plastic: UL Flammability Classification Rating 94V-0
- Device Weight: 0.003 ounces (0.085grams) SOP-8

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